NIC5004TS1, NIC5004ATS1

Self-Protected FET with Temperature and Current Limit

40 V, 6.5 A, Single N-Channel

Self-protected FETs are a series of power MOSFETs which utilize ON Semiconductor HDPlus ™ technology. The self-protected MOSFET incorporates protection features such as integrated thermal and current limits. The self-protected MOSFETs include an integrated Drain-to-Gate Clamp that provides overvoltage protection from transients and avalanche. The device is protected from Electrostatic Discharge (ESD) by utilizing an integrated Gate-to-Source Clamp.

MOSFET MAXIMUM RATINGS (T_J = 25°C unless otherwise noted)

Rating	Symbol	Value	Unit
Drain-to-Source Voltage Internally Clamped	V _{DSS}	44	Vdc
Gate-to-Source Voltage	V _{GS}	±14	Vdc
Drain Current Continuous	I _D	Internally Limited	
Operating and Storage Temperature Range (Note 1)	T _J , T _{stg}	-55 to 150	°C
Electrostatic Discharge Capability Human Body Model (HBM) Machine Model (MM)	ESD	>4000 >400	V

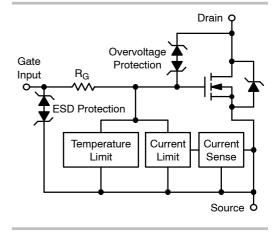
Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.



ON Semiconductor®

http://onsemi.com

V _{DSS} (Clamped)	R _{DS(on)} Typ	I _D Typ (Limited)
40 V	110 m Ω @ 10 V	6.5 A



ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 2 of this data sheet.

^{1.} Normal pre-fault operating range.

NIC5004TS1, NIC5004ATS1

MOSFET ELECTRICAL CHARACTERISTICS (T_J = 25°C unless otherwise noted) (Note 2)

Characteristic		Symbol	Min	Тур	Max	Unit
OFF CHARACTERISTICS		•			•	
Drain-to-Source Clamped Breakdown Voltage $(V_{GS} = 0 \text{ V}, I_D = 2 \text{ mA})$		V _{(BR)DSS}	36	40	44	V
Zero Gate Voltage Drain Current $(V_{DS} = 32 \text{ V}, V_{GS} = 0 \text{ V})$		I _{DSS}	-	27	100	μΑ
Gate Input Current $(V_{GS} = 5.0 \text{ V}, V_{DS} = 0 \text{ V})$		I _{GSS}	-	45	200	μΑ
ON CHARACTERISTICS						
Gate Threshold Voltage $(V_{DS} = V_{GS}, I_D = 150 \mu A)$		V _{GS(th)}	1.0	1.85	2.2	V
Static Drain-to-Source On-Res (V _{GS} = 10 V, I _D = 2.0 A)	istance	R _{DS(on)}	-	110	130	mΩ
Static Drain-to-Source On-Resistance $(V_{GS} = 5.0 \text{ V}, I_D = 2.0 \text{ A})$		R _{DS(on)}	-	130	150	mΩ
Source–Drain Forward On Voltage ($I_S = 7.0 \text{ A}, V_{GS} = 0 \text{ V}$)		V _{SD}	-	0.9	1.1	V
SELF PROTECTION CHARACTI	ERISTICS (T _J = 25°C unless otherwise noted)					
Current Limit	V_{DS} = 10 V, V_{GS} = 5.0 V, T_{J} = 25°C V_{DS} = 10 V, V_{GS} = 5.0 V, T_{J} = 100°C V_{DS} = 10 V, V_{GS} = 10 V, T_{J} = 25°C	I _{LIM}	- - -	6.5 5.5 7.9	_ _ _	А

^{2.} Wafers tested prior to sawing.

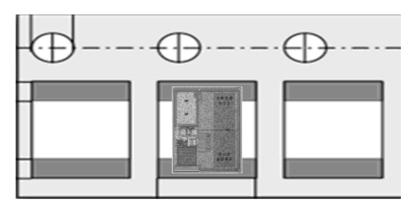
ORDERING INFORMATION

Device	Package	Shipping [†]		
NIC5004TS1	Die-in-Reel Carrier	3500 / Reel		
NIC5004ATS1	Die-in-Reel Carrier	3500 / Reel		

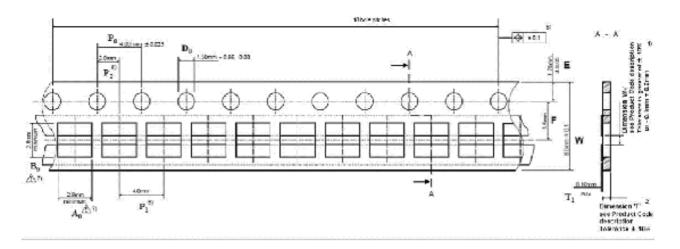
[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

NIC5004TS1, NIC5004ATS1

LAYOUT VIEW OF THE DIE IN REEL



Option B



 $W_1 = 0.7 \pm 0.2 - 0.1 \text{ mm}$ T = 0.7 mm ±/- 0.07 mm

Drawing according to ISO 8015 General tolerances ± 0.05mm

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